

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	250/310,492.2,	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:17
L2	3676	((250/310,492.2,) or (382/145,149,)) .CCLS.	USPAT	OR	OFF	2005/05/25 09:18
L3	5	2 and (semiconductor near4 topology)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L4	162	2 and (aspect near2 ratio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L5	44	4 and (contact near2 hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L6	71	4 and (inspect near4 hole or defect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:19
L7	42	6 and (electron near2 microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:20
L8	39	7 and (inspect\$3 near4 semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:21
L9	39	7 and (topology near4 semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:21

L10	58	6 and (topology near4 semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:21
L11	2	6 and (aspect adj ratio near4 value)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:22
L12	2	10 and (aspect adj ratio near4 value)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:23
L13	1	7 and (aspect adj ratio near4 value)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:23
L14	6	7 and (aspect adj ratio near4 "1.5")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/25 09:23
S1	457	Electron adj lithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/23 11:41
S2	67199	Lithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/23 11:41
S3	17257	S2 and (electron near4 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/05/23 11:42